

SWITCHMODE™ NPN Bipolar Power Transistor for Electronic Light Ballast and Switching Power Supply Applications

The MJE/MJF18204 have an application specific state-of-the-art die dedicated to the electronic ballast ("light ballast") and power supply applications.

- Improved Global Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain h_{FE}
 - Fast Switching
 - No Coil Required in Base Circuit for Fast Turn-Off (No Current Tail)
- Full Characterization at 125°C
- ON Semiconductor "6 SIGMA" Philosophy Provides Tight and Reproducible Parametric Distributions
- Two Package Choices: Standard TO-220 or Isolated TO-220

MAXIMUM RATINGS

Rating	Symbol	MJE18204	MJF18204	Unit
Collector-Emitter Voltage	V_{CEO}	600		Vdc
Collector-Base Voltage	V_{CBO}	1200		Vdc
Collector-Emitter Voltage	V_{CES}	1200		Vdc
Emitter-Base Voltage	V_{EBO}	10		Vdc
Collector Current — Continuous	I_C	5		Adc
— Peak (1)	I_{CM}	10		
Base Current — Continuous	I_B	2		Adc
— Peak (1)	I_{BM}	4		
RMS Isolation Voltage (2) (for 1 sec, R.H. ≤ 30%) $T_C = 25^\circ\text{C}$	V_{ISOL1} V_{ISOL2} V_{ISOL3}		4500 3500 1500	Volts
*Total Device Dissipation @ $T_C = 25^\circ\text{C}$ *Derate above 25°C	P_D	75 0.6	35 0.28	Watt W/°C
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150		°C

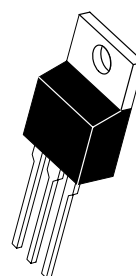
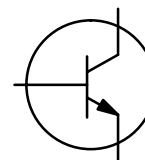
THERMAL CHARACTERISTICS

Rating	Symbol	MJE18204	MJF18204	Unit
Thermal Resistance — Junction to Case	$R_{\theta JC}$	1.65	3.55	°C/W
— Junction to Ambient	$R_{\theta JA}$	62.5	62.5	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	260		°C

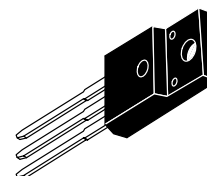
- (1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.
 (2) Proper strike and creepage distance must be provided.

MJE18204 MJF18204

POWER TRANSISTORS
5 AMPERES
1200 VOLTS
35 and 75 WATTS



CASE 221A-09
TO-220AB



CASE 221D-02
TO-220 FULLPACK

MJE18204 MJF18204

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Voltage (I _C = 1 mA, I _B = 0)	V _{CEO}	600	660		Vdc
Collector–Emitter Sustaining Voltage (I _C = 100 mA, L = 25 mH) (I _C = 200 mA, L = 25 mH, R = 2 Ω)	V _{CEO(sus)} V _{CER(sus)}	550 600	630 700		Vdc
Collector–Base Breakdown Voltage (I _{CBO} = 1 mA, I _E = 0)	V _{CBO}	1200	1300		Vdc
Emitter–Base Breakdown Voltage (I _{EBO} = 1 mA, I _C = 0)	V _{EBO}	10	12.9		Vdc
Collector Cutoff Current (V _{CE} = 600 V, I _B = 0) (V _{CE} = 550 V, I _B = 0)	@ T _C = 25°C @ T _C = 125°C	I _{CEO}		200 2000	μAdc
Collector Cutoff Current (V _{CE} = Rated V _{CES} , V _{BE} = 0) (V _{CE} = 1000 V, V _{BE} = 0)	@ T _C = 25°C @ T _C = 125°C @ T _C = 125°C	I _{CES}		100 500 100	μAdc
Collector Cutoff Current (V _{CB} = Rated V _{CB} , I _E = 0)	I _{CBO}			100	μAdc
Emitter–Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)	I _{EBO}			100	μAdc

ON CHARACTERISTICS

Base–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.1 Adc) (I _C = 2 Adc, I _B = 0.4 Adc)	V _{BE(sat)}		0.83 0.92	1.1 1.25	Vdc
Collector–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.1 Adc) (I _C = 2 Adc, I _B = 0.4 Adc)	@ T _C = 25°C @ T _C = 125°C @ T _C = 25°C @ T _C = 125°C	V _{CE(sat)}		0.3 0.7 0.3 0.8	1 1.25 0.6 1.25
DC Current Gain (I _C = 0.5 Adc, V _{CE} = 3 Vdc) (I _C = 1 Adc, V _{CE} = 1 Vdc) (I _C = 2 Adc, V _{CE} = 1 Vdc) (I _C = 5 mAdc, V _{CE} = 5 Vdc)	@ T _C = 25°C @ T _C = 125°C @ T _C = 25°C @ T _C = 125°C @ T _C = 25°C @ T _C = 125°C @ T _C = 25°C @ T _C = 125°C	h _{FE}	18 10 8 5 4 10	23 13 8 6 25 33	— 22 — —

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 MHz)	f _T		13		MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)	C _{ob}			200	pF
Input Capacitance (V _{EB} = 8 Vdc)	C _{ib}			2000	pF

DYNAMIC SATURATION VOLTAGE

Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I _{B1} reaches 90% of final I _{B1}	I _C = 2 Adc I _{B1} = 660 mAdc V _{CC} = 300 V	@ 3 μs	@ T _C = 25°C @ T _C = 125°C	V _{CE(dsat)}	2.5 7.5 7 15	V
	I _C = 2 Adc I _{B1} = 0.4 Adc V _{CC} = 300 V	@ 3 μs	@ T _C = 25°C @ T _C = 125°C			

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) continued

Characteristic	Symbol	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS: Resistive Load ($D.C. \leq 10\%$, Pulse Width = 20 μs)

Turn-on Time	$I_C = 2 \text{ Adc}, I_{B1} = 0.4 \text{ Adc}$ $I_{B2} = 1 \text{ Adc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$	t_{on}		105	175	ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$	t_{off}		1.75	2.5	μs
Turn-on Time	$I_C = 2 \text{ Adc}, I_{B1} = 0.4 \text{ Adc}$ $I_{B2} = 0.4 \text{ Adc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$	t_{on}		95	200	ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$	t_{off}		3.5	4.5	μs
Turn-on Time	$I_C = 0.7 \text{ Adc}, I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 0.4 \text{ Adc}$ $V_{CC} = 125 \text{ Vdc}$ $PW = 70 \mu\text{s}$	@ $T_C = 25^\circ\text{C}$	t_d		70	150	ns
			t_r		210	400	ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$	t_s		0.9	1.2	μs
			t_f		275	450	ns

SWITCHING CHARACTERISTICS: Inductive Load ($V_{\text{clamp}} = 300 \text{ V}$, $V_{CC} = 15 \text{ V}$, $L = 200 \mu\text{H}$)

Fall Time	$I_C = 1 \text{ Adc}$ $I_{B1} = 0.1 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f		110 95	175	ns
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		1.35 1.9	2	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_c		150 115	250	ns
Fall Time	$I_C = 2 \text{ Adc}$ $I_{B1} = 0.4 \text{ Adc}$ $I_{B2} = 1 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f		120 180	200	ns
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		1.9 2.35	2.75	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_c		190 180	300	ns
Fall Time	$I_C = 2 \text{ Adc}$ $I_{B1} = 0.4 \text{ Adc}$ $I_{B2} = 0.4 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$	t_f		185	300	ns
Storage Time		@ $T_C = 25^\circ\text{C}$	t_s		4	5	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$	t_c		350	500	ns

TYPICAL STATIC CHARACTERISTICS

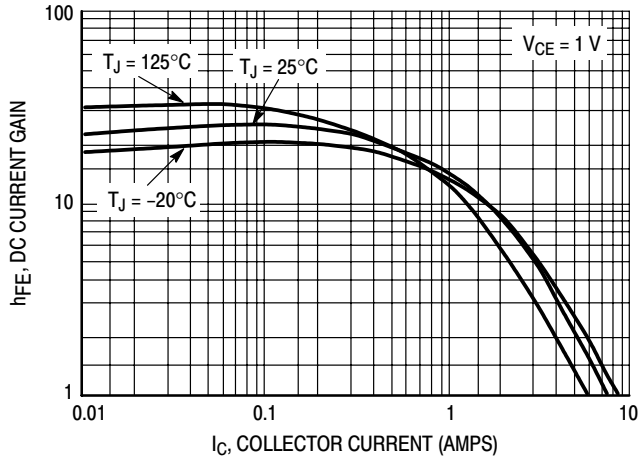


Figure 1. DC Current Gain @ 1 Volt

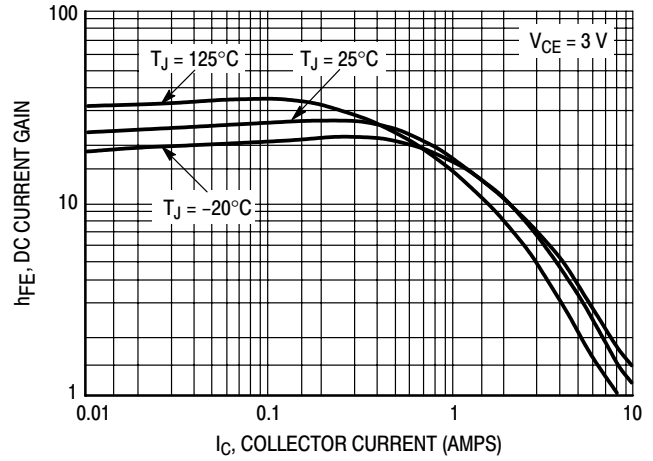


Figure 2. DC Current Gain @ 3 Volts

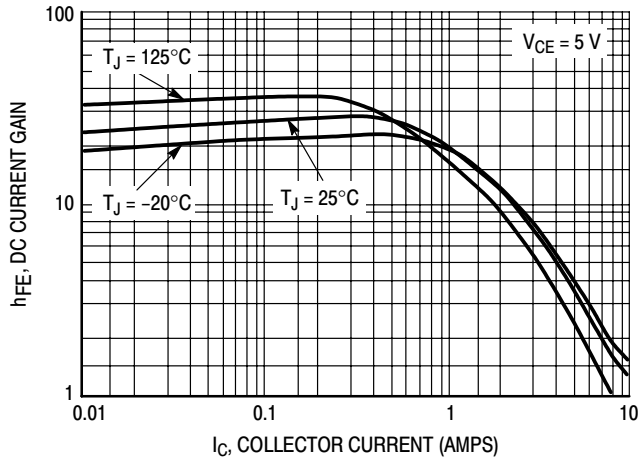


Figure 3. DC Current Gain @ 5 Volts

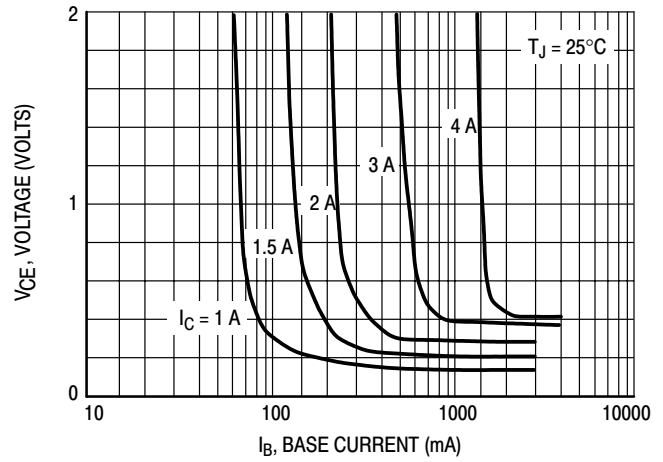


Figure 4. Collector Saturation Region

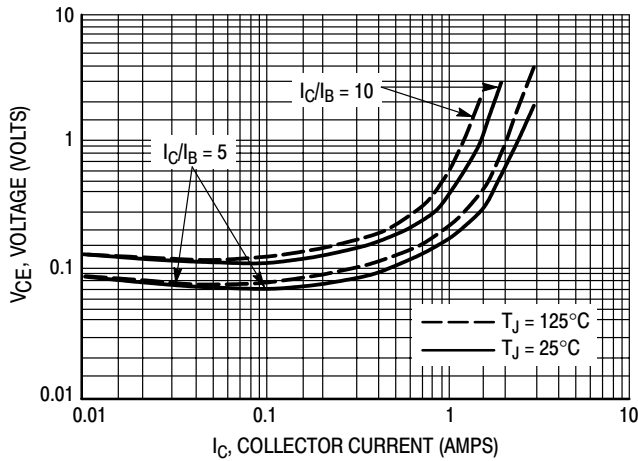


Figure 5. Collector-Emitter Saturation Voltage

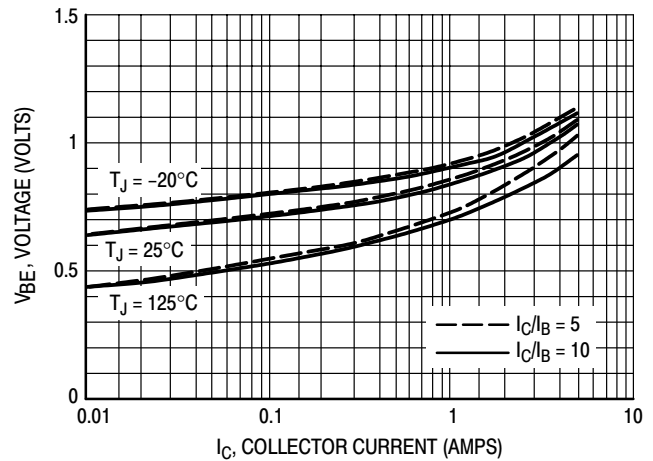


Figure 6. Base-Emitter Saturation Region

TYPICAL STATIC CHARACTERISTICS

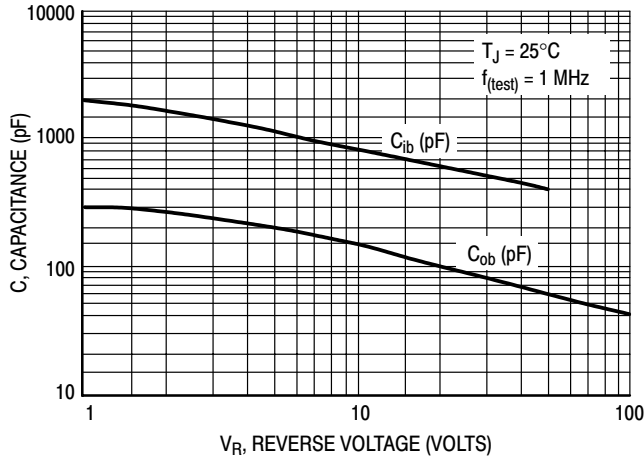


Figure 7. Capacitance

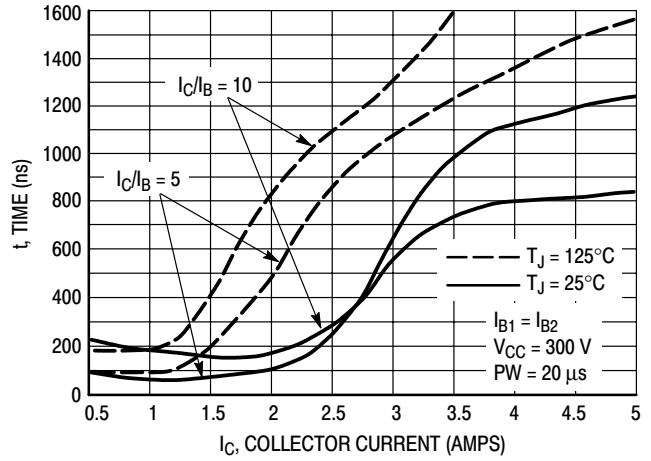


Figure 8. Resistive Switching, t_{on}

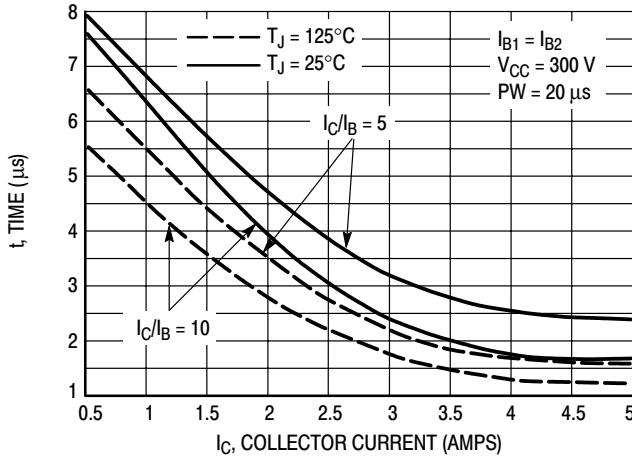


Figure 9. Resistive Switching, t_{off}

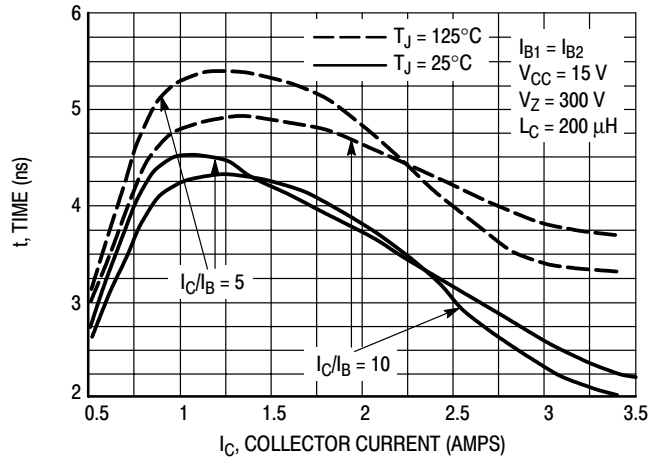


Figure 10. Inductive Storage Time, t_{si}

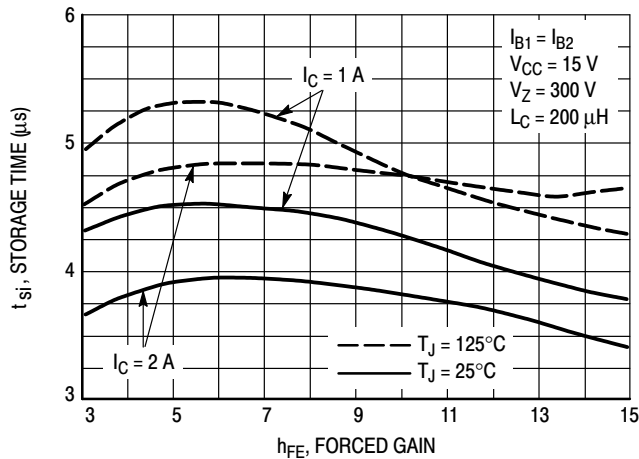


Figure 11. Inductive Storage Time, t_{si} (h_{FE})

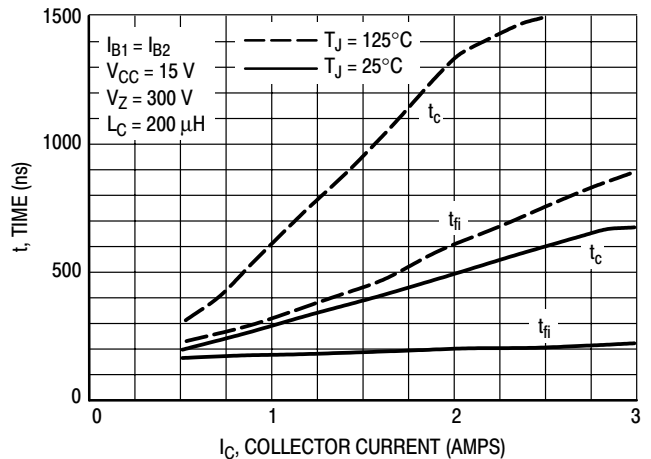


Figure 12. Inductive Switching, t_c and t_{fi} @ $I_C/I_B = 5$

TYPICAL STATIC CHARACTERISTICS

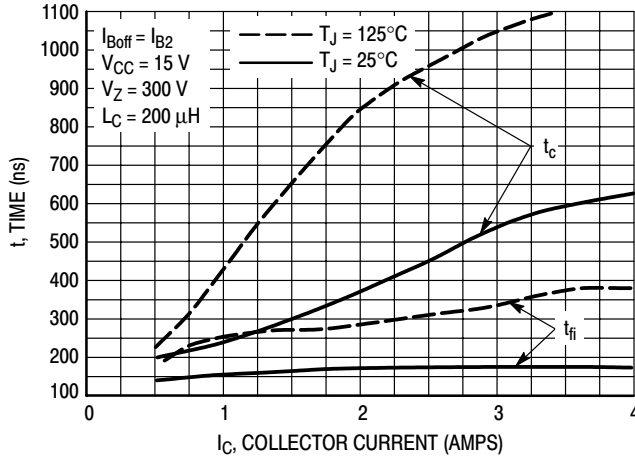


Figure 13. Inductive Switching, t_c and t_{fi} @ $I_C/I_B = 10$

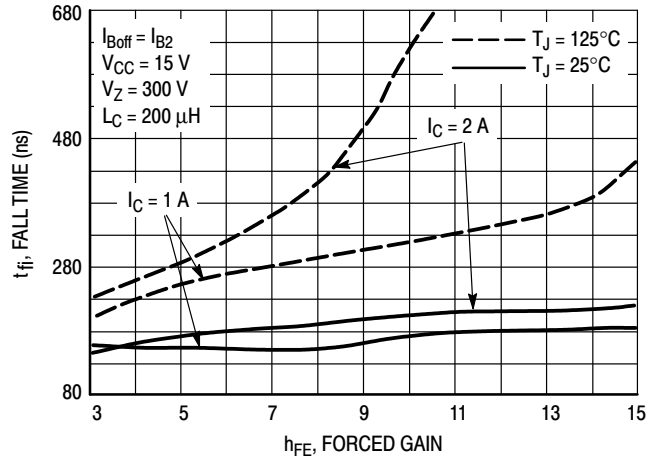


Figure 14. Inductive Fall Time

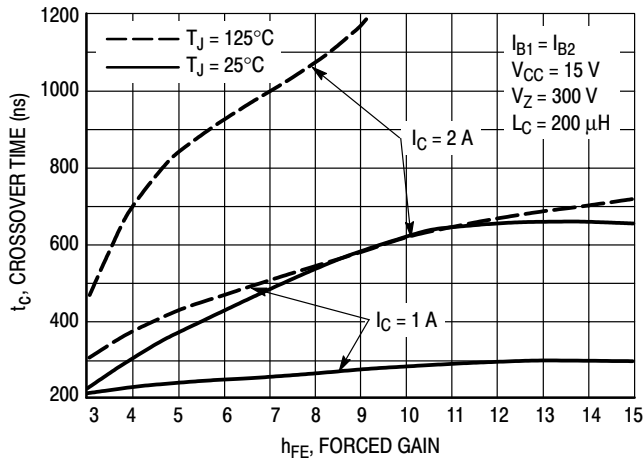


Figure 15. Inductive Crossover Time

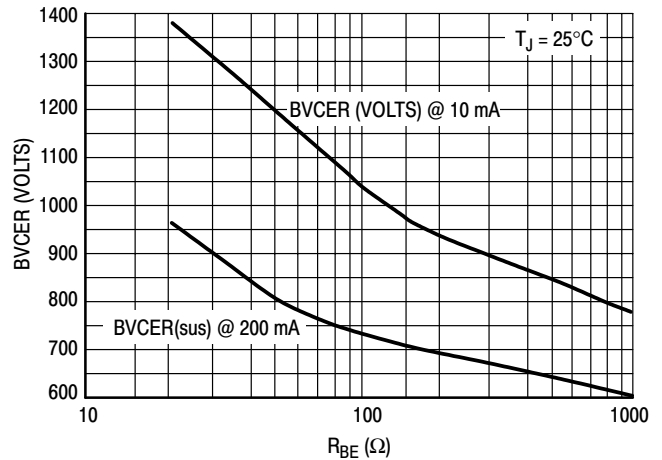


Figure 16. $BVCER = f(R_{BE})$

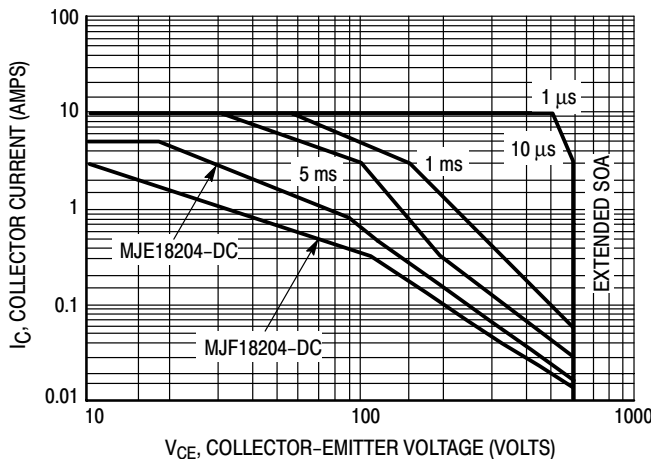


Figure 17. Forward Bias Safe Operating Area

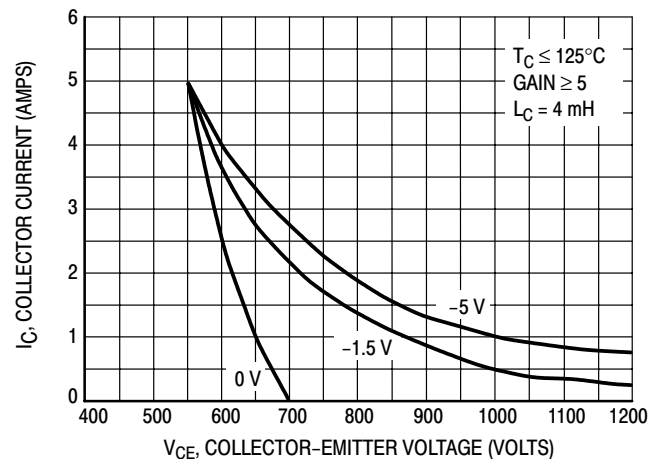


Figure 18. Reverse Bias Switching Safe Operating Area

TYPICAL STATIC CHARACTERISTICS

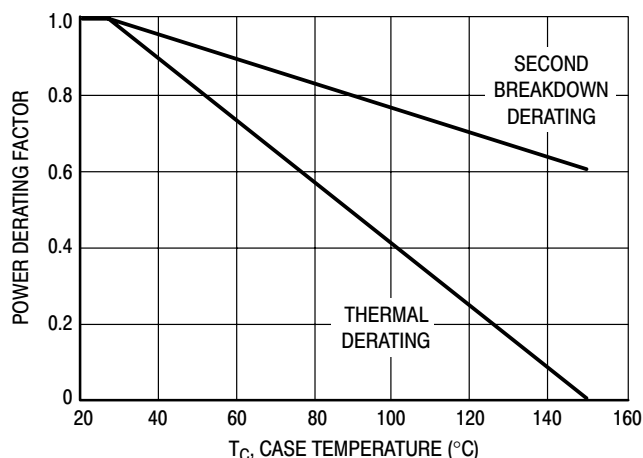


Figure 19. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 19 is based on $T_C = 25^\circ\text{C}$; $T_J(\text{pk})$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C > 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 16 may be found at any case temperature by using the appropriate curve on Figure 18.

$T_J(\text{pk})$ may be calculated from the data in Figures 21 and 22. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base-to-emitter junction reverse biased. The safe level is specified as a reverse-biased safe operating area (Figure 17). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

TYPICAL SWITCHING CHARACTERISTICS ($I_{B1} = I_{B2}$ FOR ALL CURVES)

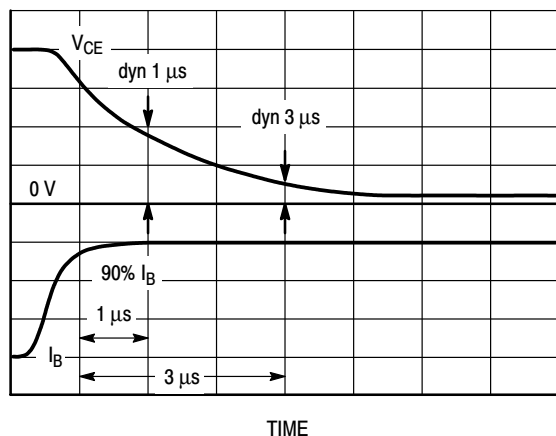


Figure 20. Dynamic Saturation Voltage Measurements

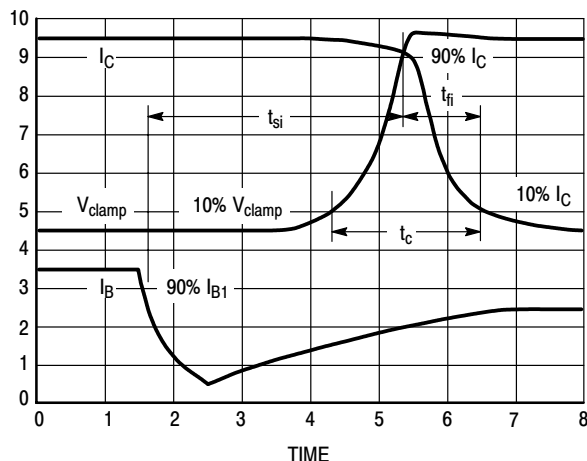
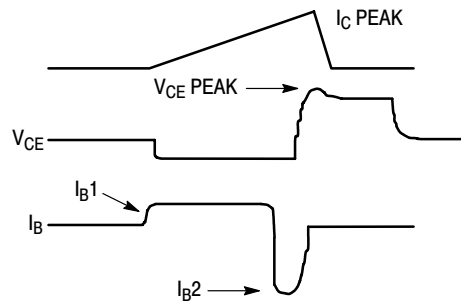
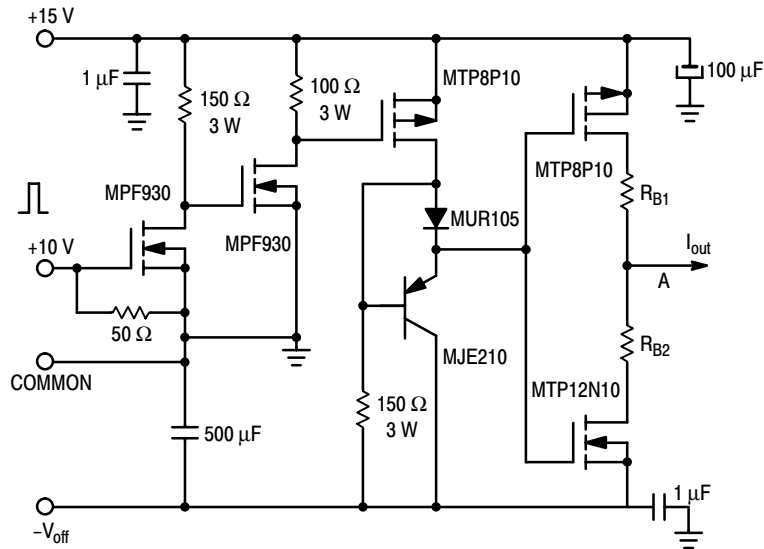


Figure 21. Inductive Switching Measurements

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TYPICAL SWITCHING CHARACTERISTICS ($I_{B1} = I_{B2}$ FOR ALL CURVES)

Table 1. Inductive Load Switching Drive Circuit



V_{(BR)CEO(sus)}
 $L = 10 \text{ mH}$
 $R_{B2} = \infty$
 $V_{CC} = 20 \text{ Volts}$
 $I_{C(pk)} = 100 \text{ mA}$

Inductive Switching
 $L = 200 \mu\text{H}$
 $R_{B2} = 0$
 $V_{CC} = 15 \text{ Volts}$
 R_{B1} selected for desired I_{B1}

RBSOA
 $L = 500 \mu\text{H}$
 $R_{B2} = 0$
 $V_{CC} = 15 \text{ Volts}$
 R_{B1} selected for desired I_{B1}

MJE18204 MJF18204

TYPICAL THERMAL RESPONSE ($I_{B1} = I_{B2}$ FOR ALL CURVES)

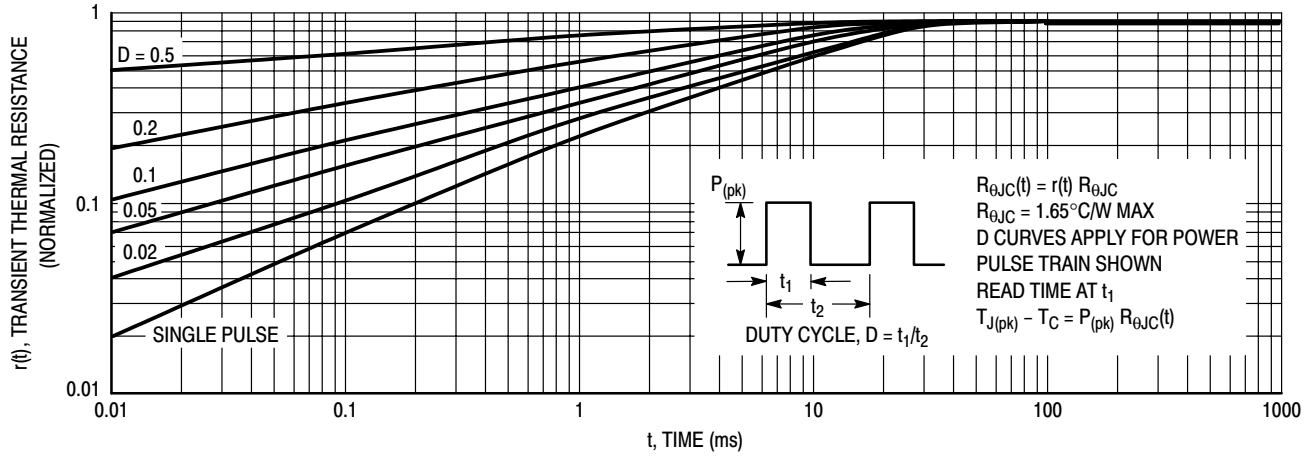


Figure 22. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18204

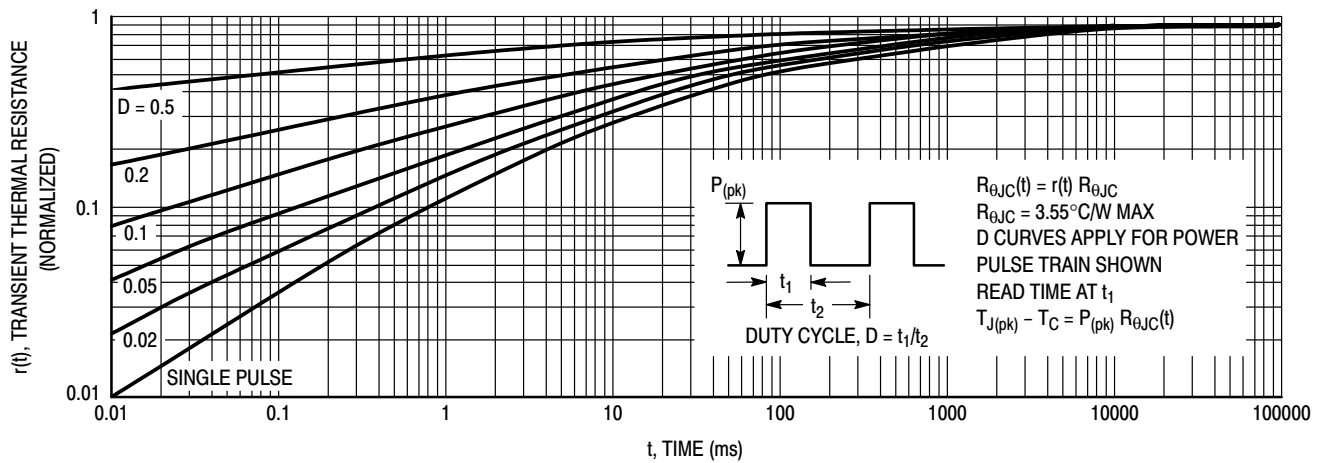


Figure 23. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJF18204

TEST CONDITIONS FOR ISOLATION TESTS*

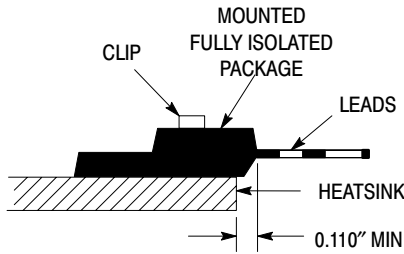


Figure 24. Screw or Clip Mounting Position for Isolation Test Number 1

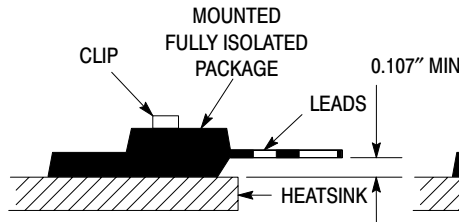


Figure 25. Clip Mounting Position for Isolation Test Number 2

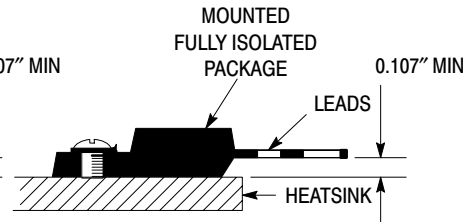


Figure 26. Screw Mounting Position for Isolation Test Number 3

*Measurement made between leads and heatsink with all leads shorted together

MOUNTING INFORMATION**

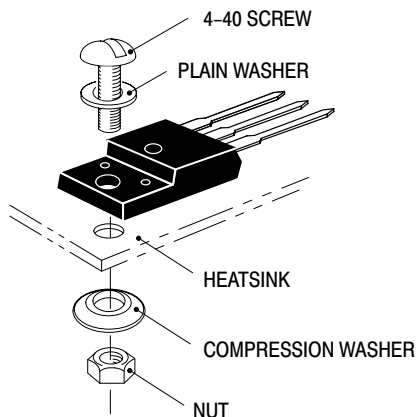


Figure 27a. Screw-Mounted

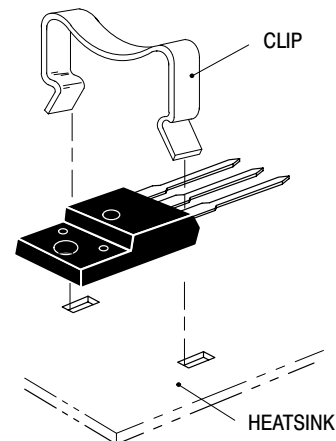


Figure 27b. Clip-Mounted

Figure 27. Typical Mounting Techniques for Isolated Package

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4-40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

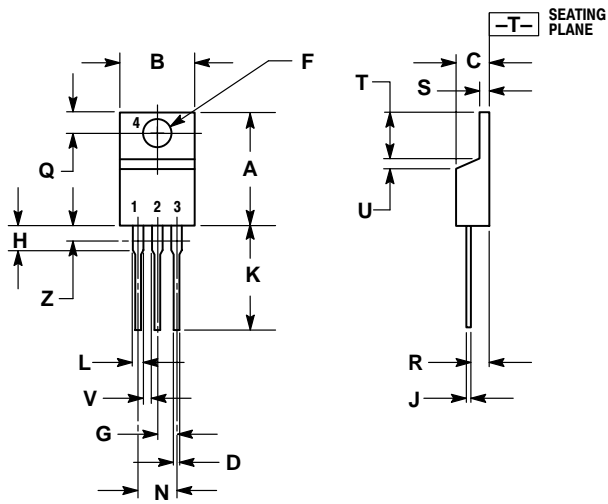
Additional tests on slotted 4-40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

** For more information about mounting power semiconductors see Application Note AN1040.

MJE18204 MJF18204

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



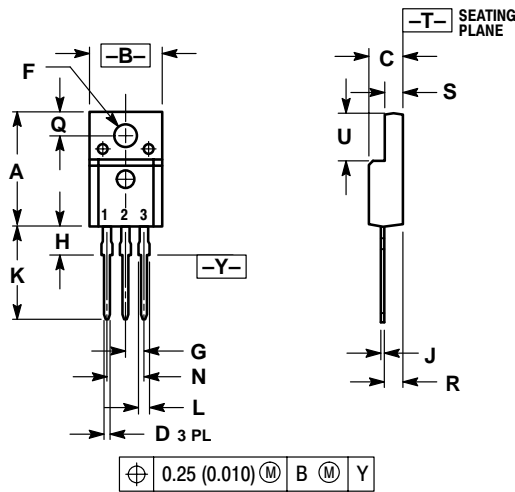
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

MJE18204 MJF18204

PACKAGE DIMENSIONS CASE 221D-02 (ISOLATED TO-220 TYPE) UL RECOGNIZED: FILE #E69369 ISSUE D



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.621	0.629	15.78	15.97
B	0.394	0.402	10.01	10.21
C	0.181	0.189	4.60	4.80
D	0.026	0.034	0.67	0.86
F	0.121	0.129	3.08	3.27
G	0.100 BSC		2.54 BSC	
H	0.123	0.129	3.13	3.27
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
N	0.200 BSC		5.08 BSC	
Q	0.126	0.134	3.21	3.40
R	0.107	0.111	2.72	2.81
S	0.096	0.104	2.44	2.64
U	0.259	0.267	6.58	6.78

STYLE 1:

1. GATE
2. DRAIN
3. SOURCE

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